CLAIMS

1. A heterojunction bipolar transistor (HBT), comprising:

    a collector mesa;

    a base mesa on the collector mesa;

    an emitter mesa on the base mesa, wherein the emitter mesa has a plurality of openings; and

    a plurality of base metals in the plurality of openings connected to the base mesa;

wherein each of the plurality of openings has a same size, and wherein the plurality of openings is at least four.

2. A method, comprising:

    providing a wafer comprising a collector mesa stack, a base mesa stack, and an emitter mesa stack;

    patterning the emitter mesa stack to form an emitter mesa having a plurality of opening;

    providing a plurality of base metals in the plurality of openings connected to the base mesa stack; and

    patterning the base mesa stack to form a base mesa;

wherein each of the plurality of openings is with a same size, and wherein the emitter mesa has 4 or more openings.